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Charge Transport Properties of BO-Chelated Azadipyrromethenes

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Charge transport properties of BO-chelated azadipyrromethenes

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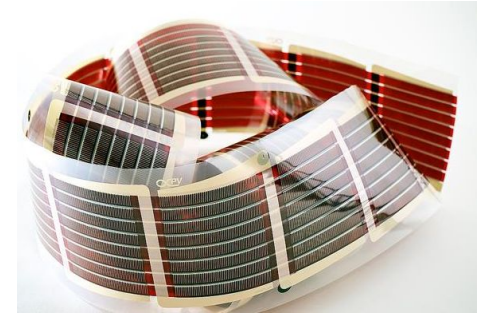
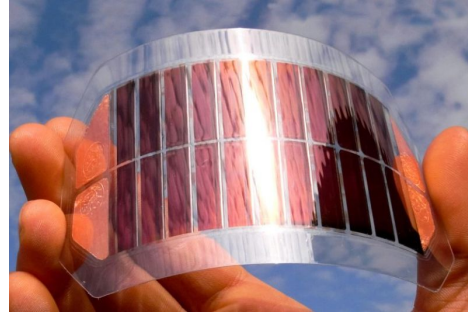
2020.12.04

Outline

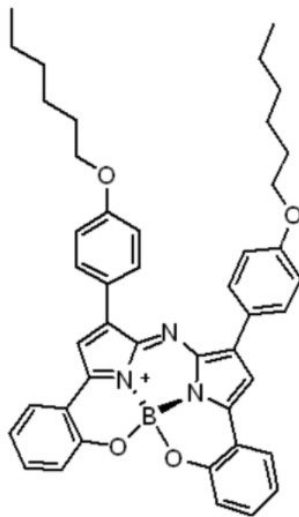
- 1. Introduction**
- 2. Device Fabrication and Thickness Measurement**
- 3. Mobility Results**
- 4. Summary and Future Plans**

Organic Solar Cells

- Flexible and light-weight
- Low cost
- Large scale fabrication

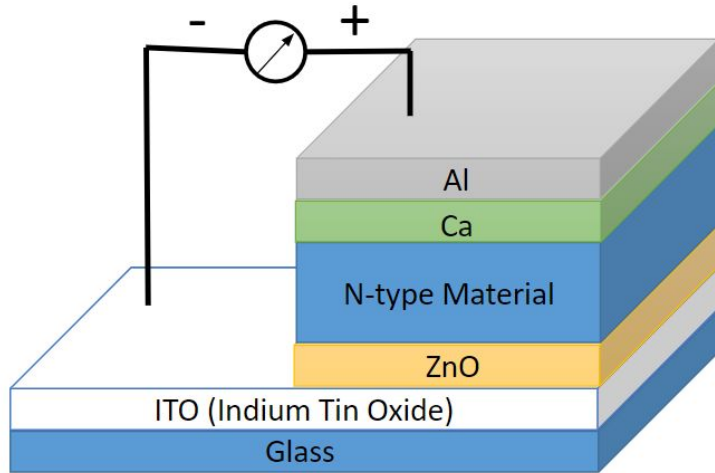


BO-chelated azadipyrromethenes Structure

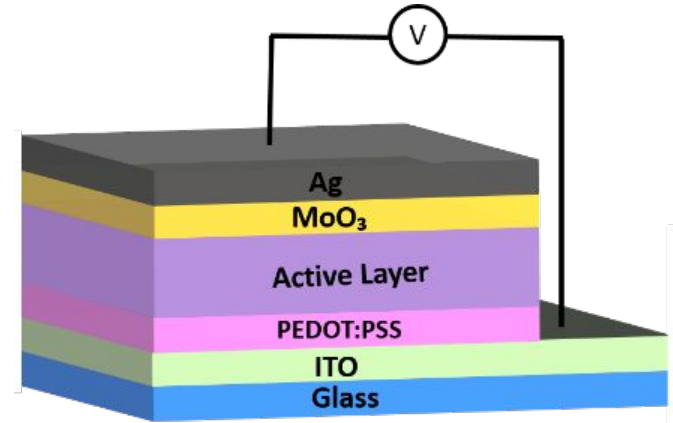


dOhexADP-BO

Mobility Device Structure



Electron Mobility Test



Hole Mobility Test

Mobility Calculation

Mott-Gurney Law

$$J = \frac{9}{8} \mu \epsilon \epsilon_0 \frac{V^2}{L^3}$$

μ	mobility
ϵ	dielectric constant
ϵ_0	permittivity of free space
d	film thickness
m	slope

$$\mu = \frac{(8m^2d^3)}{(9\epsilon\epsilon_0)}$$

Space charge-limited current behavior

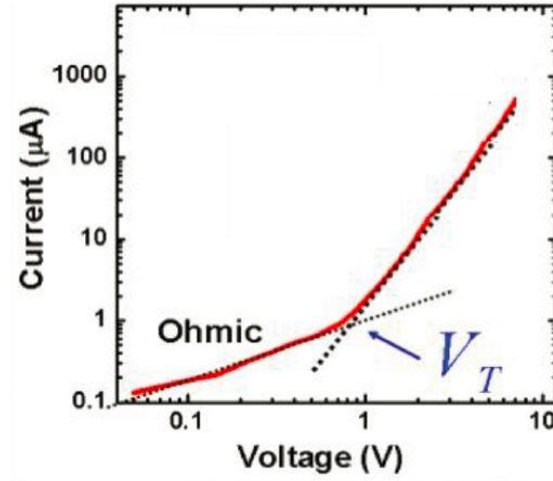
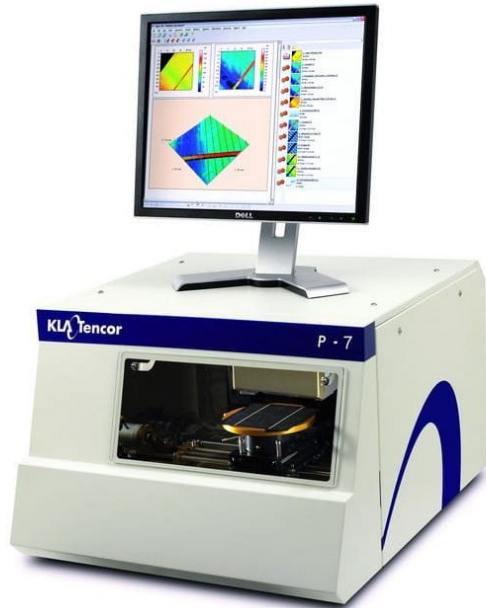


Figure 4. Space charge-limited current behavior for polymer semiconductor with only ohmic and trap-free space charge-limited current regions.

Device Fabrication (MORE Center)

- 1. Check the conductivity of ITOs.
- 2. Clean the ITOs.
- 3. Spin-coat a ZnO layer and anneal.
- 4. In glove box, spin-coat a solution of the **dOhexADP-BO** and anneal.
- 5. Thermally deposit 30nm Ca and 100nm Al for e-mobility or 10nm MoO₃ layer and 80nm Ag were thermally deposited for h-mobility

Thickness measurement



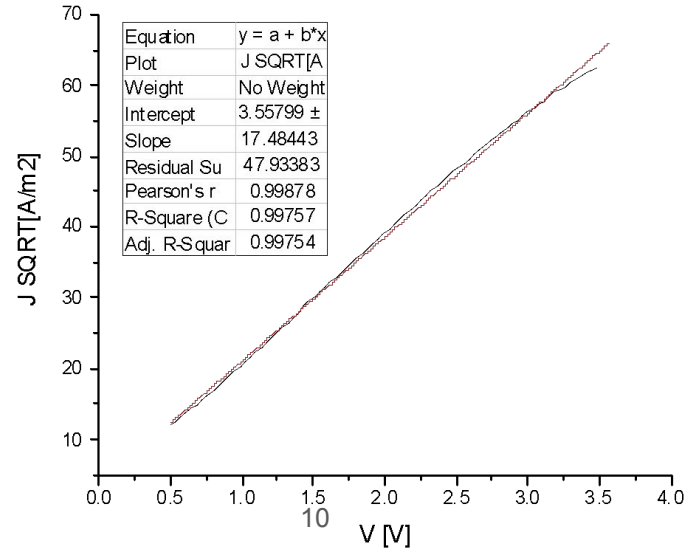
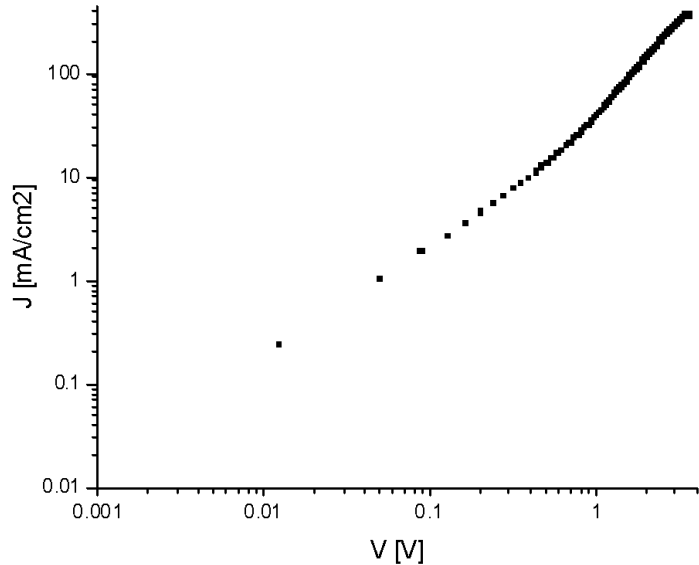
Stylus profilometer



- Use probe to detect the surface
- Moving along the surface to acquire the surface height.
- Test the difference in heights of the surfaces
- Fit the slope and thickness to calculate the mobility.

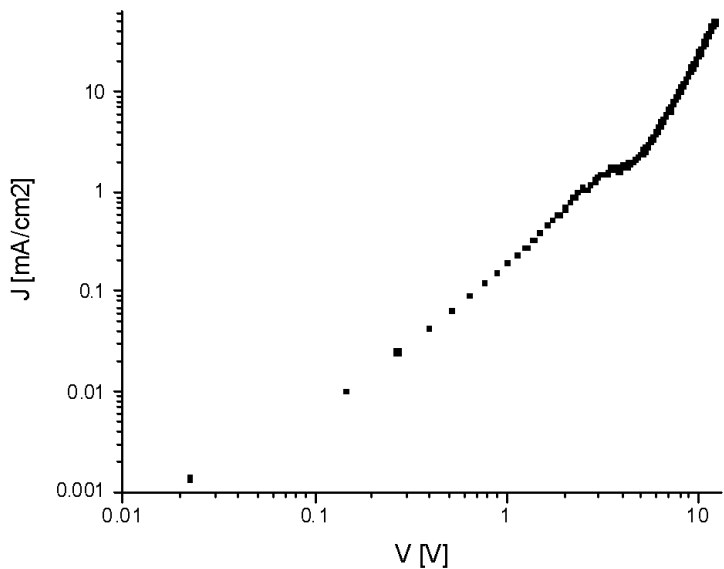
SCLC Mobility Calculations 4-2			
Equation	Units		
$J = (9/8) \mu \epsilon \epsilon_0 (V^2/d^3)$			Denominator 0.00000002
$\mu = (8m^2d^3) / (9\epsilon\epsilon_0)$	$cm^2/V\cdot s$		
Definitions		Value	Units
μ	mobility	0.0026277671	$cm^2/V\cdot s$
ϵ	dielectric constant	3	-
ϵ_0	permittivity of free space	0	F/m
d	film thickness	270	nm
		2.70E-05	cm
m	slope	19.969	

Hole Mobility Test (dOhexADP-BO)

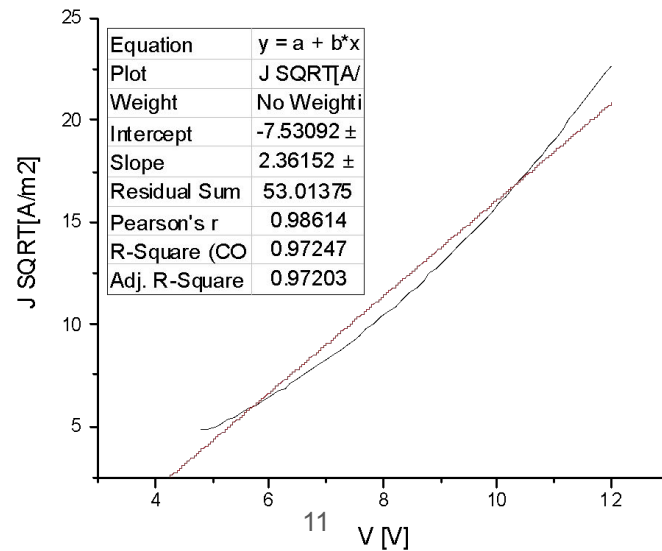


Mobility: $7.4 \cdot 10^{-4} \text{ cm}^2/\text{V} \cdot \text{s}$

Electron Mobility Test (dOhexADP-BO)



Mobility: $4.6 \cdot 10^{-6} \text{ cm}^2/\text{V}\cdot\text{s}$



Conclusions

N-type Materials	Neat μ_h ($\text{cm}^2 \text{V}^{-1}\text{s}^{-1}$)	Neat μ_e ($\text{cm}^2 \text{V}^{-1}\text{s}^{-1}$)
dOhexADP-BO	7.4×10^{-4}	4.6×10^{-6}

Summary and Future Plan

- BO-chelated materials are promising p-type semiconductors for electronic applications.
- More electron mobility tests of BO materials will be conducted.
- Continue both electron and hole mobility tests of different materials.

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